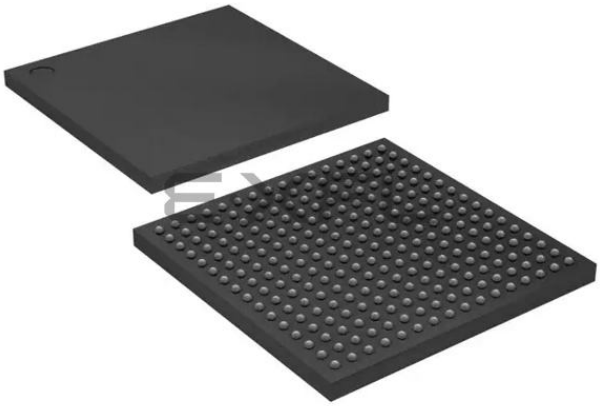

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	3125
Number of Logic Elements/Cells	50000
Total RAM Bits	1677312
Number of I/O	178
Number of Gates	-
Voltage - Supply	1.15V ~ 1.25V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/intel/10m50dcf256i7g

Contents

Operating Conditions

Intel MAX 10 devices are rated according to a set of defined parameters. To maintain the highest possible performance and reliability of the Intel MAX 10 devices, you must consider the operating requirements described in this section.

Absolute Maximum Ratings

This section defines the maximum operating conditions for Intel MAX 10 devices. The values are based on experiments conducted with the devices and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied for these conditions.

Caution: Conditions outside the range listed in the absolute maximum ratings tables may cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse effects on the device.

Single Supply Devices Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings for Intel MAX 10 Single Supply Devices

Symbol	Parameter	Min	Max	Unit
V_{CC_ONE}	Supply voltage for core and periphery through on-die voltage regulator	–0.5	3.9	V
V_{CCIO}	Supply voltage for input and output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage for phase-locked loop (PLL) regulator and analog-to-digital converter (ADC) block (analog)	–0.5	3.9	V

Dual Supply Devices Absolute Maximum Ratings

Table 3. Absolute Maximum Ratings for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Min	Max	Unit
V_{CC}	Supply voltage for core and periphery	–0.5	1.63	V
V_{CCIO}	Supply voltage for input and output buffers	–0.5	3.9	V
V_{CCA}	Supply voltage for PLL regulator (analog)	–0.5	3.41	V

continued...

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V_{CCA} (1)	Supply voltage for PLL regulator and ADC block (analog)	—	2.85/3.135	3.0/3.3	3.15/3.465	V

Dual Supply Devices Power Supplies Recommended Operating Conditions

Table 7. Power Supplies Recommended Operating Conditions for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{CC}	Supply voltage for core and periphery	—	1.15	1.2	1.25	V
V_{CCIO} (3)	Supply voltage for input and output buffers	3.3 V	3.135	3.3	3.465	V
		3.0 V	2.85	3	3.15	V
		2.5 V	2.375	2.5	2.625	V
		1.8 V	1.71	1.8	1.89	V
		1.5 V	1.425	1.5	1.575	V
		1.35 V	1.2825	1.35	1.4175	V
		1.2 V	1.14	1.2	1.26	V
V_{CCA}(4)	Supply voltage for PLL regulator (analog)	—	2.375	2.5	2.625	V
V_{CCD_PLL}(5)	Supply voltage for PLL regulator (digital)	—	1.15	1.2	1.25	V
V_{CCA_ADC}	Supply voltage for ADC analog block	—	2.375	2.5	2.625	V
V_{CCINT}	Supply voltage for ADC digital block	—	1.15	1.2	1.25	V

(3) V_{CCIO} for all I/O banks must be powered up during user mode because V_{CCIO} I/O banks are used for the ADC and I/O functionalities.

(4) All V_{CCA} pins must be powered to 2.5 V (even when PLLs are not used), and must be powered up and powered down at the same time.

(5) V_{CCD_PLL} must always be connected to V_{CC} through a decoupling capacitor and ferrite bead.

Recommended Operating Conditions

Table 8. Recommended Operating Conditions for Intel MAX 10 Devices

Symbol	Parameter	Condition	Min	Max	Unit
V_I	DC input voltage	—	–0.5	3.6	V
V_O	Output voltage for I/O pins	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial	0	85	°C
		Industrial	–40(6)	100	°C
		Automotive	–40(6)	125	°C
t_{RAMP}	Power supply ramp time	—	(7)	10	ms
I_{Diode}	Magnitude of DC current across PCI* clamp diode when enabled	—	—	10	mA

Programming/Erasure Specifications

Table 9. Programming/Erasure Specifications for Intel MAX 10 Devices

This table shows the programming cycles and data retention duration of the user flash memory (UFM) and configuration flash memory (CFM) blocks.

For more information about data retention duration with 10,000 programming cycles for automotive temperature devices, contact your Intel quality representative.

Erase and reprogram cycles (E/P) (8) (Cycles/page)	Temperature (°C)	Data retention duration (Years)
10,000	85	20
10,000	100	10

(6) –40°C is only applicable to Start of Test, when the device is powered-on. The device does not stay at the minimum junction temperature for a long time.

(7) There is no absolute minimum value for the ramp time requirement. Intel characterized the minimum ramp time at 200 µs.

(8) The number of E/P cycles applies to the smallest possible flash block that can be erased or programmed in each Intel MAX 10 device. Each Intel MAX 10 device has multiple flash pages per device.

DC Characteristics

Supply Current and Power Consumption

Intel offers two ways to estimate power for your design—the Excel-based Early Power Estimator (EPE) and the Intel Quartus Prime Power Analyzer feature.

Use the Excel-based EPE before you start your design to estimate the supply current for your design. The EPE provides a magnitude estimate of the device power because these currents vary greatly with the usage of the resources.

The Intel Quartus Prime Power Analyzer provides better quality estimates based on the specifics of the design after you complete place-and-route. The Power Analyzer can apply a combination of user-entered, simulation-derived, and estimated signal activities that, when combined with detailed circuit models, yield very accurate power estimates.

Related Information

- Early Power Estimator User Guide
  Provides more information about power estimation tools.
- Power Analysis chapter, Intel Quartus Prime Handbook
  Provides more information about power estimation tools.

I/O Pin Leakage Current

The values in the table are specified for normal device operation. The values vary during device power-up. This applies for all V_{CCIO} settings (3.3, 3.0, 2.5, 1.8, 1.5, 1.35, and 1.2 V).

10 µA I/O leakage current limit is applicable when the internal clamping diode is off. A higher current can be the observed when the diode is on.

Input channel leakage of ADC I/O pins due to hot socket is up to maximum of 1.8 mA. The input channel leakage occurs when the ADC IP core is enabled or disabled. This is applicable to all Intel MAX 10 devices with ADC IP core, which are 10M04, 10M08, 10M16, 10M25, 10M40, and 10M50 devices. The ADC I/O pins are in Bank 1A.

Table 10. I/O Pin Leakage Current for Intel MAX 10 Devices

Symbol	Parameter	Condition	Min	Max	Unit
I_I	Input pin leakage current	V_I = 0 V to $V_{CCIOMAX}$	–10	10	µA
I_{OZ}	Tristated I/O pin leakage current	V_O = 0 V to $V_{CCIOMAX}$	–10	10	µA

Table 15. OCT Variation after Calibration at Device Power-Up for Intel MAX 10 Devices

This table lists the change percentage of the OCT resistance with voltage and temperature.

Description	Nominal Voltage	dR/dT (%/°C)	dR/dV (%/mV)
OCT variation after calibration at device power-up	3.00	0.25	–0.027
	2.50	0.245	–0.04
	1.80	0.242	–0.079
	1.50	0.235	–0.125
	1.35	0.229	–0.16
	1.20	0.197	–0.208

Figure 1. Equation for OCT Resistance after Calibration at Device Power-Up

$$\Delta R_V = (V_2 - V_1) \times 1000 \times dR/dV$$

$$\Delta R_T = (T_2 - T_1) \times dR/dT$$

$$\text{For } \Delta R_X < 0; MF_X = 1/(|\Delta R_X|/100 + 1)$$

$$\text{For } \Delta R_X > 0; MF_X = \Delta R_X/100 + 1$$

$$MF = MF_V \times MF_T$$

$$R_{final} = R_{initial} \times MF$$

The definitions for equation are as follows:

- T_1 is the initial temperature.
- T_2 is the final temperature.
- MF is multiplication factor.
- $R_{initial}$ is initial resistance.
- R_{final} is final resistance.

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{PLL_PSERR}	Accuracy of PLL phase shift	—	—	—	±50	ps
t_{ARESET}	Minimum pulse width on areset signal.	—	10	—	—	ns
$t_{CONFIGPLL}$	Time required to reconfigure scan chains for PLLs	—	—	3.5 (32)	—	SCANCLK cycles
$f_{SCANCLK}$	scanclk frequency	—	—	—	100	MHz

Table 28. PLL Specifications for Intel MAX 10 Single Supply Devices

For V36 package, the PLL specification is based on single supply devices.

Symbol	Parameter	Condition	Max	Unit
$t_{OUTJITTER\_PERIOD\_DEDCLK}$ (31)	Dedicated clock output period jitter	$F_{OUT} \geq 100$ MHz	660	ps
		$F_{OUT} < 100$ MHz	66	mUI
$t_{OUTJITTER\_CCJ\_DEDCLK}$ (31)	Dedicated clock output cycle-to-cycle jitter	$F_{OUT} \geq 100$ MHz	660	ps
		$F_{OUT} < 100$ MHz	66	mUI

Table 29. PLL Specifications for Intel MAX 10 Dual Supply Devices

Symbol	Parameter	Condition	Max	Unit
$t_{OUTJITTER\_PERIOD\_DEDCLK}$ (31)	Dedicated clock output period jitter	$F_{OUT} \geq 100$ MHz	300	ps
		$F_{OUT} < 100$ MHz	30	mUI
$t_{OUTJITTER\_CCJ\_DEDCLK}$ (31)	Dedicated clock output cycle-to-cycle jitter	$F_{OUT} \geq 100$ MHz	300	ps
		$F_{OUT} < 100$ MHz	30	mUI

(32) With 100 MHz scanclk frequency.

Parameter		Symbol	Condition	Min	Typ	Max	Unit
Conversion Rate [52]	Conversion time	—	Single measurement	—	—	1	Cycle
			Continuous measurement	—	—	1	Cycle
			Temperature measurement	—	—	1	Cycle

Related Information

SPICE Models for Intel FPGAs

Periphery Performance Specifications

This section describes the periphery performance, high-speed I/O, and external memory interface.

Actual achievable frequency depends on design and system specific factors. Ensure proper timing closure in your design and perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specifications

For more information about the high-speed and low-speed I/O performance pins, refer to the respective device pin-out files.

Related Information

Documentation: Pin-Out Files for Intel FPGAs

[52] For more detailed description, refer to the Timing section in the *Intel MAX 10 Analog-to-Digital Converter User Guide*.

True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications

Single Supply Devices True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications

Table 37. True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices

True **RSDS** transmitter is only supported at bottom I/O banks. Emulated **RSDS** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	50	5	—	50	5	—	50	MHz
		×8	5	—	50	5	—	50	5	—	50	MHz
		×7	5	—	50	5	—	50	5	—	50	MHz
		×4	5	—	50	5	—	50	5	—	50	MHz
		×2	5	—	50	5	—	50	5	—	50	MHz
		×1	5	—	100	5	—	100	5	—	100	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	100	100	—	100	100	—	100	Mbps
		×8	80	—	100	80	—	100	80	—	100	Mbps
		×7	70	—	100	70	—	100	70	—	100	Mbps
		×4	40	—	100	40	—	100	40	—	100	Mbps
		×2	20	—	100	20	—	100	20	—	100	Mbps
		×1	10	—	100	10	—	100	10	—	100	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	50	5	—	50	5	—	50	MHz
		×8	5	—	50	5	—	50	5	—	50	MHz
		×7	5	—	50	5	—	50	5	—	50	MHz
		×4	5	—	50	5	—	50	5	—	50	MHz
		×2	5	—	50	5	—	50	5	—	50	MHz
		×1	5	—	100	5	—	100	5	—	100	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	100	100	—	100	100	—	100	Mbps

continued...

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
		×8	80	—	100	80	—	100	80	—	100	Mbps
		×7	70	—	100	70	—	100	70	—	100	Mbps
		×4	40	—	100	40	—	100	40	—	100	Mbps
		×2	20	—	100	20	—	100	20	—	100	Mbps
		×1	10	—	100	10	—	100	10	—	100	Mbps
t_{DUTY}	Duty cycle on transmitter output clock	—	45	—	55	45	—	55	45	—	55	%
TCCS(55)	Transmitter channel-to-channel skew	—	—	—	300	—	—	300	—	—	300	ps
$t_{x\ Jitter}$(56)	Output jitter (high-speed I/O performance pin)	—	—	—	425	—	—	425	—	—	425	ps
	Output jitter (low-speed I/O performance pin)	—	—	—	470	—	—	470	—	—	470	ps
t_{RISE}	Rise time	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{FALL}	Fall time	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{LOCK}	Time required for the PLL to lock, after CONF_DONE signal goes high, indicating the completion of device configuration	—	—	—	1	—	—	1	—	—	1	ms

(55) TCCS specifications apply to I/O banks from the same side only.

(56) TX jitter is the jitter induced from core noise and I/O switching noise.

Dual Supply Devices True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications

Table 38. True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

True **RSDS** transmitter is only supported at bottom I/O banks. Emulated **RSDS** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	155	5	—	155	5	—	155	MHz
		×8	5	—	155	5	—	155	5	—	155	MHz
		×7	5	—	155	5	—	155	5	—	155	MHz
		×4	5	—	155	5	—	155	5	—	155	MHz
		×2	5	—	155	5	—	155	5	—	155	MHz
		×1	5	—	310	5	—	310	5	—	310	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	310	100	—	310	100	—	310	Mbps
		×8	80	—	310	80	—	310	80	—	310	Mbps
		×7	70	—	310	70	—	310	70	—	310	Mbps
		×4	40	—	310	40	—	310	40	—	310	Mbps
		×2	20	—	310	20	—	310	20	—	310	Mbps
		×1	10	—	310	10	—	310	10	—	310	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	150	5	—	150	5	—	150	MHz
		×8	5	—	150	5	—	150	5	—	150	MHz
		×7	5	—	150	5	—	150	5	—	150	MHz
		×4	5	—	150	5	—	150	5	—	150	MHz
		×2	5	—	150	5	—	150	5	—	150	MHz
		×1	5	—	300	5	—	300	5	—	300	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	300	100	—	300	100	—	300	Mbps
		×8	80	—	300	80	—	300	80	—	300	Mbps
		×7	70	—	300	70	—	300	70	—	300	Mbps

continued...

Emulated RSDS_E_1R Transmitter Timing Specifications

Table 39. Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

Emulated **RSDS_E_1R** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	85	5	—	85	5	—	85	MHz
		×8	5	—	85	5	—	85	5	—	85	MHz
		×7	5	—	85	5	—	85	5	—	85	MHz
		×4	5	—	85	5	—	85	5	—	85	MHz
		×2	5	—	85	5	—	85	5	—	85	MHz
		×1	5	—	170	5	—	170	5	—	170	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	170	100	—	170	100	—	170	Mbps
		×8	80	—	170	80	—	170	80	—	170	Mbps
		×7	70	—	170	70	—	170	70	—	170	Mbps
		×4	40	—	170	40	—	170	40	—	170	Mbps
		×2	20	—	170	20	—	170	20	—	170	Mbps
		×1	10	—	170	10	—	170	10	—	170	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	85	5	—	85	5	—	85	MHz
		×8	5	—	85	5	—	85	5	—	85	MHz
		×7	5	—	85	5	—	85	5	—	85	MHz
		×4	5	—	85	5	—	85	5	—	85	MHz
		×2	5	—	85	5	—	85	5	—	85	MHz
		×1	5	—	170	5	—	170	5	—	170	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	170	100	—	170	100	—	170	Mbps
		×8	80	—	170	80	—	170	80	—	170	Mbps
		×7	70	—	170	70	—	170	70	—	170	Mbps

continued...

True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications

Table 40. True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices

True **mini-LVDS** transmitter is only supported at the bottom I/O banks. Emulated **mini-LVDS_E_3R** transmitter is supported at the output pin of all I/O banks.

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK}	Input clock frequency (high-speed I/O performance pin)	×10	5	—	155	5	—	155	5	—	155	MHz
		×8	5	—	155	5	—	155	5	—	155	MHz
		×7	5	—	155	5	—	155	5	—	155	MHz
		×4	5	—	155	5	—	155	5	—	155	MHz
		×2	5	—	155	5	—	155	5	—	155	MHz
		×1	5	—	310	5	—	310	5	—	310	MHz
HSIODR	Data rate (high-speed I/O performance pin)	×10	100	—	310	100	—	310	100	—	310	Mbps
		×8	80	—	310	80	—	310	80	—	310	Mbps
		×7	70	—	310	70	—	310	70	—	310	Mbps
		×4	40	—	310	40	—	310	40	—	310	Mbps
		×2	20	—	310	20	—	310	20	—	310	Mbps
		×1	10	—	310	10	—	310	10	—	310	Mbps
f_{HSCLK}	Input clock frequency (low-speed I/O performance pin)	×10	5	—	150	5	—	150	5	—	150	MHz
		×8	5	—	150	5	—	150	5	—	150	MHz
		×7	5	—	150	5	—	150	5	—	150	MHz
		×4	5	—	150	5	—	150	5	—	150	MHz
		×2	5	—	150	5	—	150	5	—	150	MHz
		×1	5	—	300	5	—	300	5	—	300	MHz
HSIODR	Data rate (low-speed I/O performance pin)	×10	100	—	300	100	—	300	100	—	300	Mbps
		×8	80	—	300	80	—	300	80	—	300	Mbps

continued...

Symbol	Parameter	Mode	–I6, –A6, –C7, –I7			–A7			–C8			Unit
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
		×7	70	—	300	70	—	300	70	—	300	Mbps
		×4	40	—	300	40	—	300	40	—	300	Mbps
		×2	20	—	300	20	—	300	20	—	300	Mbps
		×1	10	—	300	10	—	300	10	—	300	Mbps
t_{DUTY}	Duty cycle on transmitter output clock	—	45	—	55	45	—	55	45	—	55	%
TCCS[61]	Transmitter channel-to-channel skew	—	—	—	300	—	—	300	—	—	300	ps
$t_{x\ Jitter}$[62]	Output jitter (high-speed I/O performance pin)	—	—	—	425	—	—	425	—	—	425	ps
	Output jitter (low-speed I/O performance pin)	—	—	—	470	—	—	470	—	—	470	ps
t_{RISE}	Rise time	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{FALL}	Fall time	20 – 80%, C_{LOAD} = 5 pF	—	500	—	—	500	—	—	500	—	ps
t_{LOCK}	Time required for the PLL to lock, after `CONF_DONE` signal goes high, indicating the completion of device configuration	—	—	—	1	—	—	1	—	—	1	ms

(61) TCCS specifications apply to I/O banks from the same side only.

(62) TX jitter is the jitter induced from core noise and I/O switching noise.

Memory Output Clock Jitter Specifications

Intel MAX 10 devices support external memory interfaces up to 303 MHz. The external memory interfaces for Intel MAX 10 devices calibrate automatically.

The memory output clock jitter measurements are for 200 consecutive clock cycles.

The clock jitter specification applies to memory output clock pins generated using DDIO circuits clocked by a PLL output routed on a PHY clock network.

DDR3 and LPDDR2 SDRAM memory interfaces are only supported on the fast speed grade device.

Table 48. Memory Output Clock Jitter Specifications for Intel MAX 10 Devices

Parameter	Symbol	–6 Speed Grade		–7 Speed Grade		Unit
		Min	Max	Min	Max	
Clock period jitter	$t_{JIT(per)}$	–127	127	–215	215	ps
Cycle-to-cycle period jitter	$t_{JIT(cc)}$	—	242	—	360	ps

Related Information

Literature: External Memory Interfaces
Provides more information about external memory system performance specifications, board design guidelines, timing analysis, simulation, and debugging information.

Configuration Specifications

This section provides configuration specifications and timing for Intel MAX 10 devices.

JTAG Timing Parameters

Table 49. JTAG Timing Parameters for Intel MAX 10 Devices

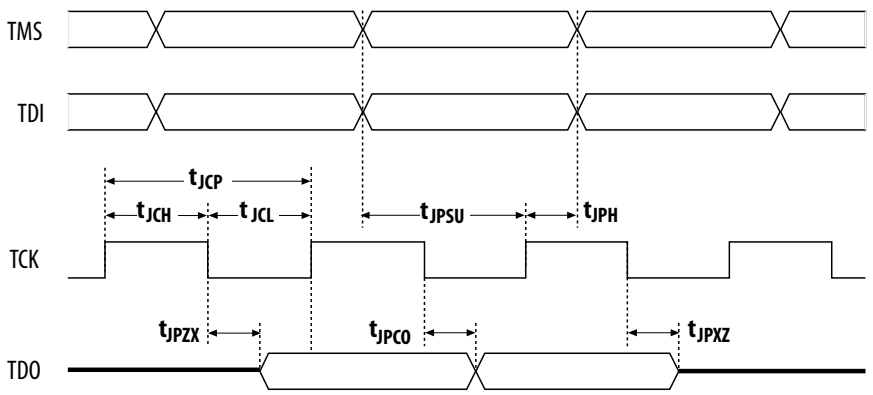
The values are based on C_L = 10 pF of TDO.

The affected Boundary Scan Test (BST) instructions are SAMPLE/PRELOAD, EXTEST, INTEST, and CHECK_STATUS.

Symbol	Parameter	Non-BST and non-CONFIG_IO Operation		BST and CONFIG_IO Operation		Unit
		Minimum	Maximum	Minimum	Maximum	
t_{JCP}	TCK clock period	40	—	50	—	ns
t_{JCH}	TCK clock high time	20	—	25	—	ns
t_{JCL}	TCK clock low time	20	—	25	—	ns
t_{JPSU_TDI}	JTAG port setup time	2	—	2	—	ns
t_{JPSU_TMS}	JTAG port setup time	3	—	3	—	ns
t_{JPH}	JTAG port hold time	10	—	10	—	ns
t_{JPCO}	JTAG port clock to output	—	• 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) • 17 (for V_{CCIO} = 1.8 and 1.5 V)	—	• 18 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) • 20 (for V_{CCIO} = 1.8 and 1.5 V)	ns
t_{JPZX}	JTAG port high impedance to valid output	—	• 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) • 17 (for V_{CCIO} = 1.8 and 1.5 V)	—	• 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) • 17 (for V_{CCIO} = 1.8 and 1.5 V)	ns
t_{JPXZ}	JTAG port valid output to high impedance	—	• 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) • 17 (for V_{CCIO} = 1.8 and 1.5 V)	—	• 15 (for V_{CCIO} = 3.3, 3.0, and 2.5 V) • 17 (for V_{CCIO} = 1.8 and 1.5 V)	ns

Glossary

Table 59. Glossary

Term	Definition
JTAG Timing Specifications	
R_L	Receiver differential input discrete resistor (external to Intel MAX 10 devices).
RSKM (Receiver input skew margin)	HIGH-SPEED I/O block: The total margin left after accounting for the sampling window and TCCS. RSKM = (TUI – SW – TCCS) / 2.
Sampling window (SW)	HIGH-SPEED I/O Block: The period of time during which the data must be valid to capture it correctly. The setup and hold times determine the ideal strobe position in the sampling window.
Single-ended voltage referenced I/O standard	The AC input signal values indicate the voltage levels at which the receiver must meet its timing specifications. The DC input signal values indicate the voltage levels at which the final logic state of the receiver is unambiguously defined. After the receiver input crosses the AC value, the receiver changes to the new logic state. The new logic state is then maintained as long as the input stays beyond the DC threshold. This approach is intended to provide predictable receiver timing in the presence of input waveform ringing.
t_C	High-speed receiver/transmitter input and output clock period.
TCCS (Channel-to- channel-skew)	HIGH-SPEED I/O block: The timing difference between the fastest and slowest output edges, including t_{CO} variation and clock skew. The clock is included in the TCCS measurement.
t_{cin}	Delay from clock pad to I/O input register.
t_{CO}	Delay from clock pad to I/O output.
t_{cout}	Delay from clock pad to I/O output register.

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Term	Definition
V_{OCM}	Output common mode voltage: The common mode of the differential signal at the transmitter.
V_{OD}	Output differential voltage swing: The difference in voltage between the positive and complementary conductors of a differential transmission line at the transmitter. $V_{OD} = V_{OH} – V_{OL}$.
V_{OH}	Voltage output high: The maximum positive voltage from an output which the device considers is accepted as the minimum positive high level.
V_{OL}	Voltage output low: The maximum positive voltage from an output which the device considers is accepted as the maximum positive low level.
V_{OS}	Output offset voltage: $V_{OS} = (V_{OH} + V_{OL}) / 2$.
$V_{OX\ (AC)}$	AC differential Output cross point voltage: The voltage at which the differential output signals must cross.
V_{REF}	Reference voltage for SSTL, HSTL, and HSUL I/O Standards.
$V_{REF(AC)}$	AC input reference voltage for SSTL, HSTL, and HSUL I/O Standards. $V_{REF(AC)} = V_{REF(DC)}$ + noise. The peak-to-peak AC noise on V_{REF} should not exceed 2% of $V_{REF(DC)}$.
$V_{REF(DC)}$	DC input reference voltage for SSTL, HSTL, and HSUL I/O Standards.
$V_{SWING\ (AC)}$	AC differential input voltage: AC Input differential voltage required for switching.
$V_{SWING\ (DC)}$	DC differential input voltage: DC Input differential voltage required for switching.
V_{TT}	Termination voltage for SSTL, HSTL, and HSUL I/O Standards.
$V_{X\ (AC)}$	AC differential Input cross point voltage: The voltage at which the differential input signals must cross.

Document Revision History for the Intel MAX 10 FPGA Device Datasheet

Document Version	Changes
2018.06.29	• Removed links on instant-on feature. • Added JTAG timing specifications term in *Glossary*. • Renamed the following IP cores as per Intel rebranding: — Renamed Altera Modular ADC IP core to Modular ADC core Intel FPGA IP core. — Renamed Altera Modular Dual ADC IP core to Modular Dual ADC core Intel FPGA IP core.

Date	Version	Changes
January 2016	2016.01.22	• Added description about automotive temperature devices in the Programming/Erasure Specifications table. • Changed the pin capacitance to maximum values. • Updated maximum TCCS specifications from 410 ps to 300 ps in the following tables: — True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices — Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices • Added new table: True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Single Supply Devices. • Updated maximum f_{HSCLK} and HSIODR specifications for –A6, –C7, and –I7 speed grades in True LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices table. • Updated SW specifications in the following tables: — LVDS Receiver Timing Specifications for Intel MAX 10 Single Supply Devices — LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for Intel MAX 10 Dual Supply Devices • Updated maximum f_{HSCLK} and HSIODR (high-speed I/O performance pin) specifications for –I6, –A6, –C7, –I7 speed grades in LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for Intel MAX 10 Dual Supply Devices table. • Removed Internal Configuration Time information in the Uncompressed .rbf Sizes for Intel MAX 10 Devices table. • Added Internal Configuration Time tables for uncompressed `.rbf` files and compressed `.rbf` files. • Removed Preliminary tags for all tables.
November 2015	2015.11.02	• Added description to *Maximum Allowed Overshoot During Transitions over a 11.4-Year Time Frame* topic. • Added ADC_VREF Pin Leakage Current for Intel MAX 10 Devices table. • Updated the condition for "Bus-hold high, sustaining current" parameter from "$V_{IN} < V_{IL}$ (minimum)" to "$V_{IN} < V_{IH}$ (minimum)" in Bus Hold Parameters table.

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Date	Version	Changes
		• Added –A6 speed grade in the following tables: — Intel MAX 10 Device Grades and Speed Grades Supported — Series OCT without Calibration Specifications for Intel MAX 10 Devices — Clock Tree Specifications for Intel MAX 10 Devices — Embedded Multiplier Specifications for Intel MAX 10 Devices — Memory Block Performance Specifications for Intel MAX 10 Devices — True PPDS and Emulated PPDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True RSDS and Emulated RSDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated RSDS_E_1R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True Mini-LVDS and Emulated Mini-LVDS_E_3R Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — True LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — Emulated LVDS_E_3R, SLVS, and Sub-LVDS Transmitter Timing Specifications for Intel MAX 10 Dual Supply Devices — LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for Intel MAX 10 Dual Supply Devices — IOE Programmable Delay on Row Pins for Intel MAX 10 Devices — IOE Programmable Delay on Column Pins for Intel MAX 10 Devices • Updated the maximum value for input clock cycle-to-cycle jitter ($t_{INJITTER\_CCJ}$) with F_{INPFD} < 100 MHz condition from 750 ps to ±750 ps in PLL Specifications for Intel MAX 10 Devices table. • Updated the dual supply mode performance in Embedded Multiplier Specifications for Intel MAX 10 Devices table. • Updated the dual supply mode performance in Memory Block Performance Specifications for Intel MAX 10 Devices table. • Added typical specifications in Internal Oscillator Frequencies for Intel MAX 10 Devices table. • Updated specifications in UFM Performance Specifications for Intel MAX 10 Devices table. • Updated sampling window specifications in LVDS, TMDS, HiSpi, SLVS, and Sub-LVDS Receiver Timing Specifications for Intel MAX 10 Dual Supply Devices table. • Updated IOE programmable delay for row and column pins. • Changed instances of *Quartus II* to *Quartus Prime*.
June 2015	2015.06.12	• Updated the maximum values in Internal Weak Pull-Up Resistor for Intel MAX 10 Devices table. • Removed Internal Weak Pull-Up Resistor equation. • Updated the note for input resistance and input capacitance parameters in the ADC Performance Specifications table for both single supply and dual supply devices. Note: Download the SPICE models for simulation. • Added a note to AC Accuracy - THD, SNR, and SINAD parameters in the ADC Performance Specifications for Intel MAX 10 Dual Supply Devices table. Note: When using internal V_{REF}, THD = 66 dB, SNR = 58 dB and SINAD = 57.5 dB for dedicated ADC input channels. • Updated clock period jitter and cycle-to-cycle period jitter parameters in the Memory Output Clock Jitter Specifications for Intel MAX 10 Devices table.

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